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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

TAKAFUJI et al

Atty. Ref.: 1035-501

Serial No. 10/802,735

Group: 2811

Filed: March 18, 2004

Examiner:

For: SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME

\* \* \* \* \*

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

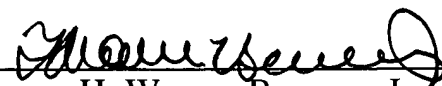
Sir:

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**


Further to applicants' Information Disclosure Statement of June 7, 2004, applicants herewith submit a corrected Form PTO-1449 (i.e., the page numbers of the Tong et al reference and the date of the Vandooren et al reference has been corrected).

Respectfully submitted,  
NIXON & VANDERHYE P.C.

June 25, 2004

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<b>INFORMATION DISCLOSURE</b> <b>SITUATION</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.	SERIAL NO.
	1035-501	10/802,735
	APPLICANT	
	TAKAFUJI et al	
	FILING DATE	GROUP
	March 18, 2004	2811

## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (including Author, Title, Date, Pertinent pages, etc.)

	Salerno et al, "Single Crystal Silicon AMLCDs", Conference Record of the 1994 International Display Research Conference (IDRC) (1994), pp. 39-44
	Tong et al, "Semiconductor Wafer Bonding: Science and Technology", John Wiley & Sons, Inc., New York, 1999, pp. 8-11, 48-55, 58-65, 108 and 109
	Warner et al, "Low-Temperature Oxide-Bonded Three-Dimensional Integrated Circuits", 2002 IEEE International SOI Conference, October 2002, pp. 123-125
	Allen et al, "SOI Uniformity and Surface Smoothness Improvement Using GCIB Processing", 2002 IEEE International SOI Conference, October 2002, pp. 192-193
	Matsumoto et al, "70 nm SOI-CMOS of 135 GHz $f_{\max}$ with Dual Offset-Implanted Source-Drain Extension Structure for RF/Analog and Logic Applications", International Electron Device Meeting, December 2001, pp. 219-222
	Vandooren et al, "Scaling Assessment of Fully-Depleted SOI Technology at the 30nm Gate Length Generation", 2002 IEEE international SOI Conference Proceedings, October 2002, pp. 25-27

\*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.